

## Description

The PSM8N10R12D uses split gate trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. This device is suitable for power management and high efficiency applications at high switching frequencies applications.

### MOSFET Product Summary

$V_{DS}(V)$	$R_{DS(on)}(m\Omega)(Typ)$	$I_D(A)$
100	8.5@ $V_{GS} = 10V$	68
	10.7@ $V_{GS} = 4.5V$	

## Feature

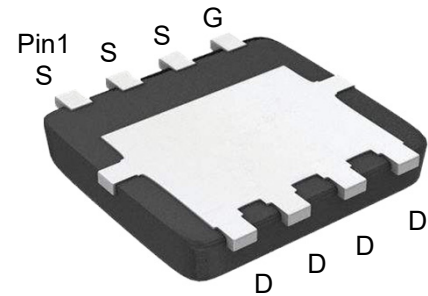
- Low  $R_{DS(ON)}$  - Ensures On-State Losses are Minimized
- Excellent  $Q_{gd} \times R_{DS(ON)}$  Product(FOM)
- Advanced Technology for DC-DC Converts
- Small Form Factor Thermally Efficient Package  
Enables Higher Density End Products
- 100% UIS (Avalanche) Rated
- Lead-Free Finish ; RoHS Compliant
- Halogen and Antimony Free. "Green" Device

## Applications

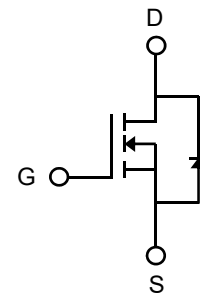
- PWM applications
- Load switch
- Power management
- DC-DC Converters
- Wireless Chargers

## Absolute maximum rating@25°C

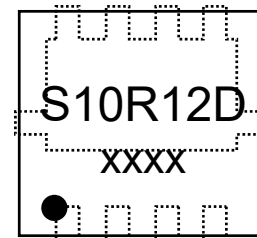
Rating	Symbol	Value	Units
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous <sup>1)</sup>	$I_D$	$T_C=25^\circ C$	68
		$T_C=100^\circ C$	43
Pulsed Drain Current <sup>2)</sup>	$I_{DM}$	270	A
Total Power Dissipation <sup>3)</sup>	$P_D$	92.6	W
Avalanche Current <sup>4)</sup>	$I_{AS}$	25	A
Avalanche Energy <sup>4)</sup>	$E_{AS}$	158	mJ
Thermal Resistance , Junction-to-Case <sup>5)</sup>	$R_{\theta JC}$	1.4	$^\circ C/W$
Thermal Resistance Junction-to-Ambient <sup>6)</sup>	$R_{\theta JA}$	44.5	$^\circ C/W$
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~+150	$^\circ C$



PDFN5060-8L  
(Bottom View)



Circuit Diagram



Pin1

Marking (Top View)

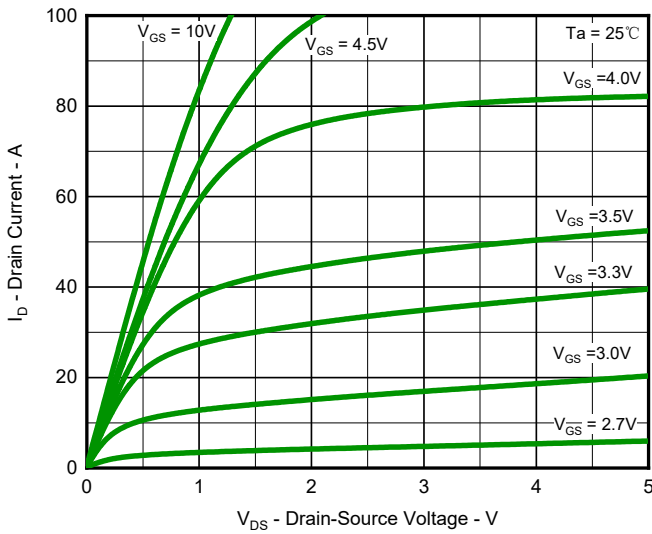
## Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 100V, V_{GS} = 0V$	-	-	1.0	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.2	1.8	2.2	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 20A$	-	8.5	10.6	m $\Omega$
		$V_{GS} = 4.5V, I_D = 15A$	-	10.7	13.5	
<b>Dynamic Characteristics<sup>7)</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 50V, V_{GS} = 0V,$ $f = 1.0MHz$	-	1244	-	pF
Output Capacitance	$C_{oss}$		-	395	-	
Reverse Transfer Capacitance	$C_{rss}$		-	14	-	
<b>Switching Characteristics<sup>7)</sup></b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS} = 50V, V_{GS} = 10V,$ $I_D = 20A, R_{GEN} = 3\Omega$	-	5.7	-	ns
Turn-on Rise Time	$t_r$		-	4.0	-	
Turn-Off Delay Time	$t_{d(off)}$		-	20.7	-	
Turn-Off Fall Time	$t_f$		-	10.5	-	
Total Gate Charge	$Q_g$	$V_{DS} = 50V, V_{GS} = 10V,$ $I_D = 20A$	-	21.4	-	nC
Gate-Source Charge	$Q_{gs}$		-	3.2	-	
Gate-Drain Charge	$Q_{gd}$		-	8.0	-	
Gate Resistance	$R_g$	$V_{GS}=0V, V_{DS}=0V, f=1MHz$	-	1.1	-	$\Omega$
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0V, I_S = 20A$	0.5	0.87	1.0	V

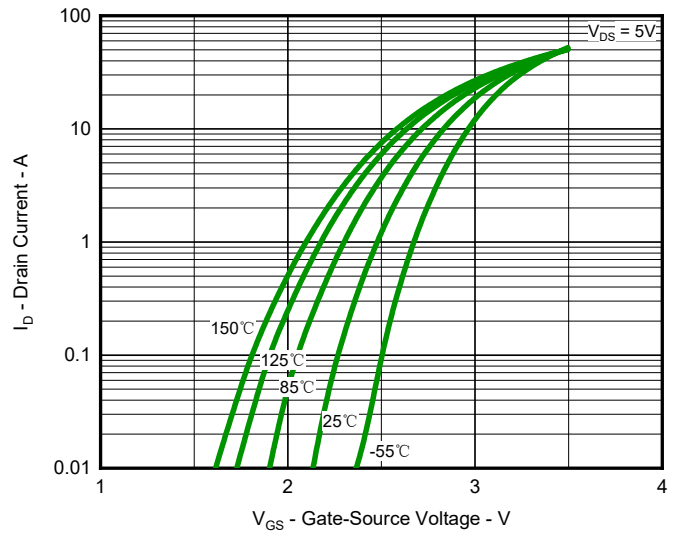
## Notes:

1. Computed continuous current assumes the condition of  $T_{J\_Max}$  while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. Repetitive Rating: Pulse width limited by maximum junction temperature( $T_{J\_Max}=150^\circ C$ ).
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. This single-pulse measurement was taken under the following condition [ $L=0.5mH, V_{GS}=10V, V_{DS}=80V$ ]while it's value is limited by  $T_{J\_Max}=150^\circ C$ .
5. Device mounted on infinite heatsink.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
7. Guaranteed by design, not subject to production.

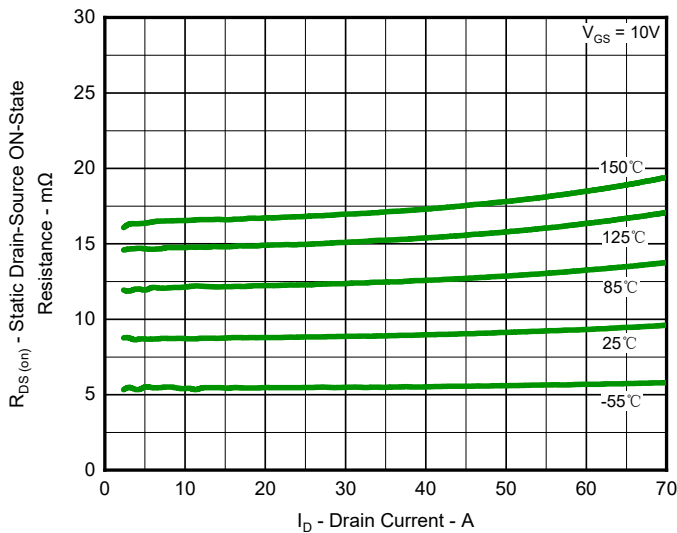
## Typical Characteristics



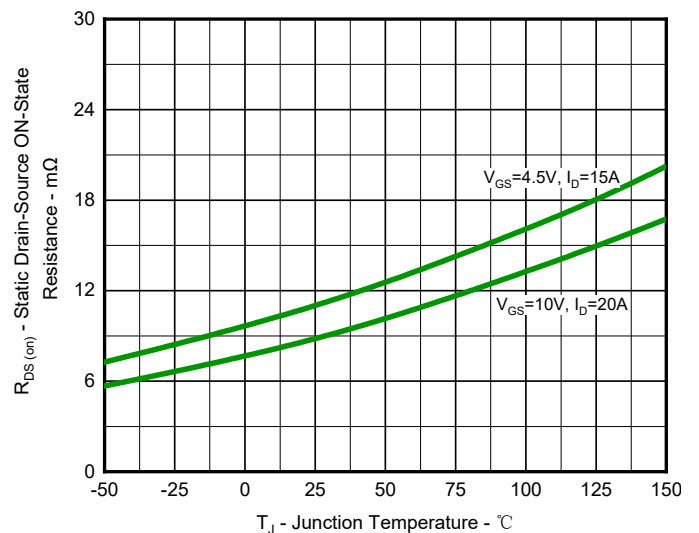
**Fig.1 Output Characteristics**



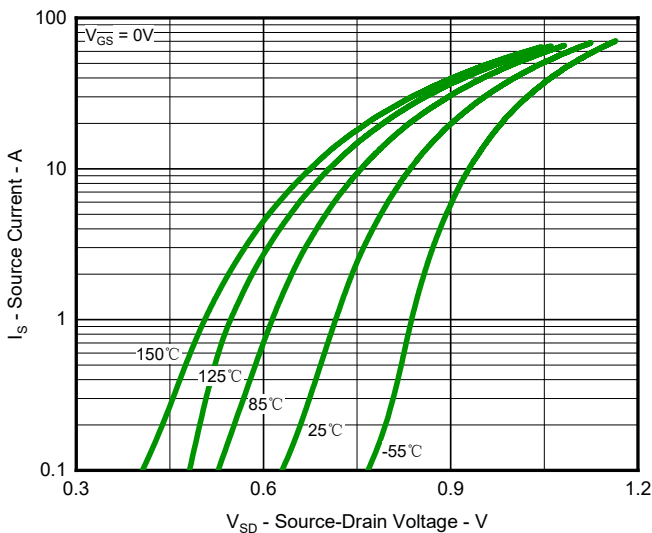
**Fig.2 Typical Transfer Characteristic**



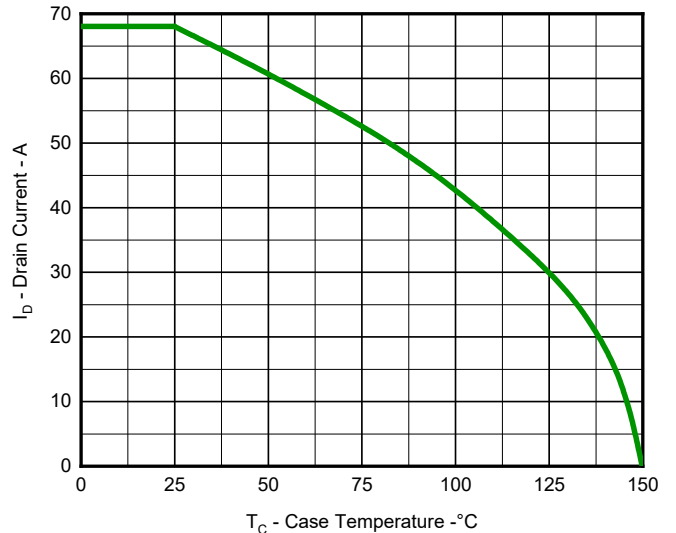
**Fig.3 Typical On-Resistance vs Drain Current and Temperature**



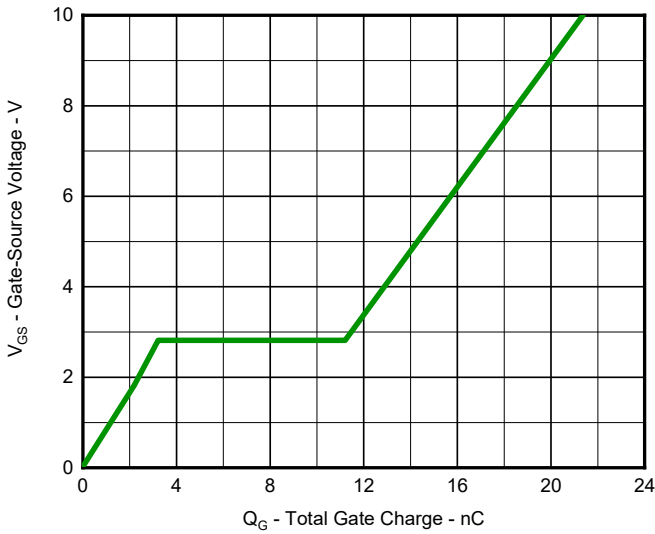
**Fig.4 On-Resistance Variation with Temperature**



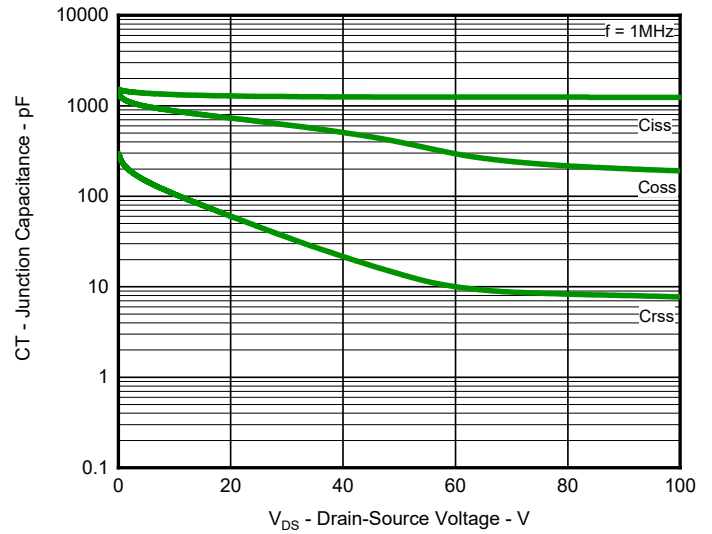
**Fig.5 Diode Forward Voltage vs. Current**



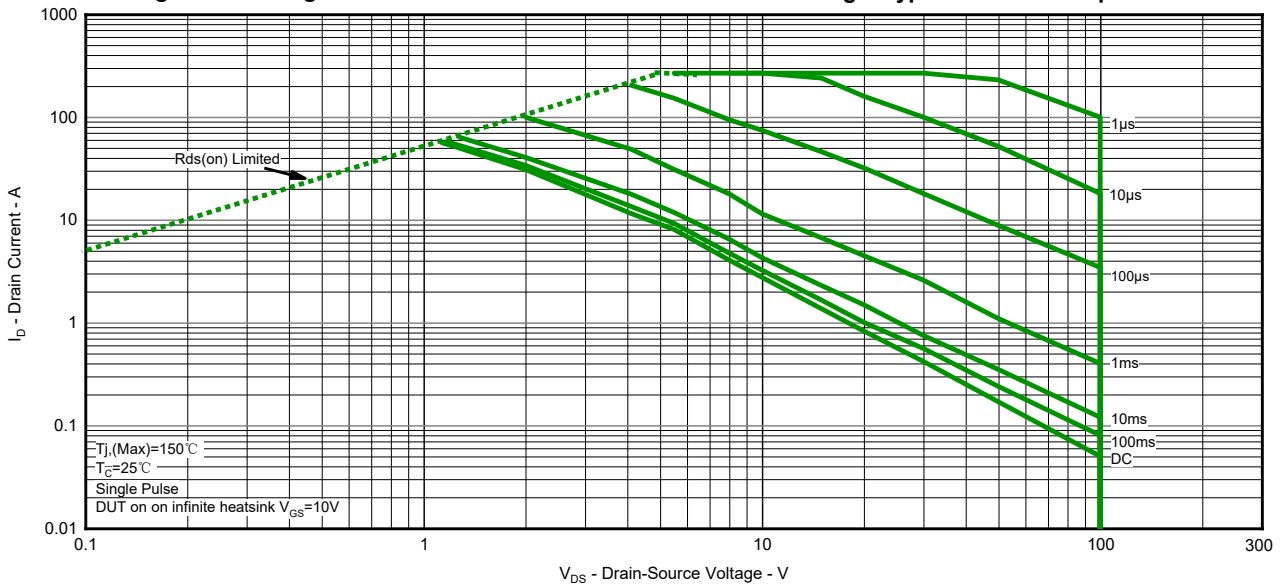
**Fig.6 Maximum Drain Current vs. Case Temperature**



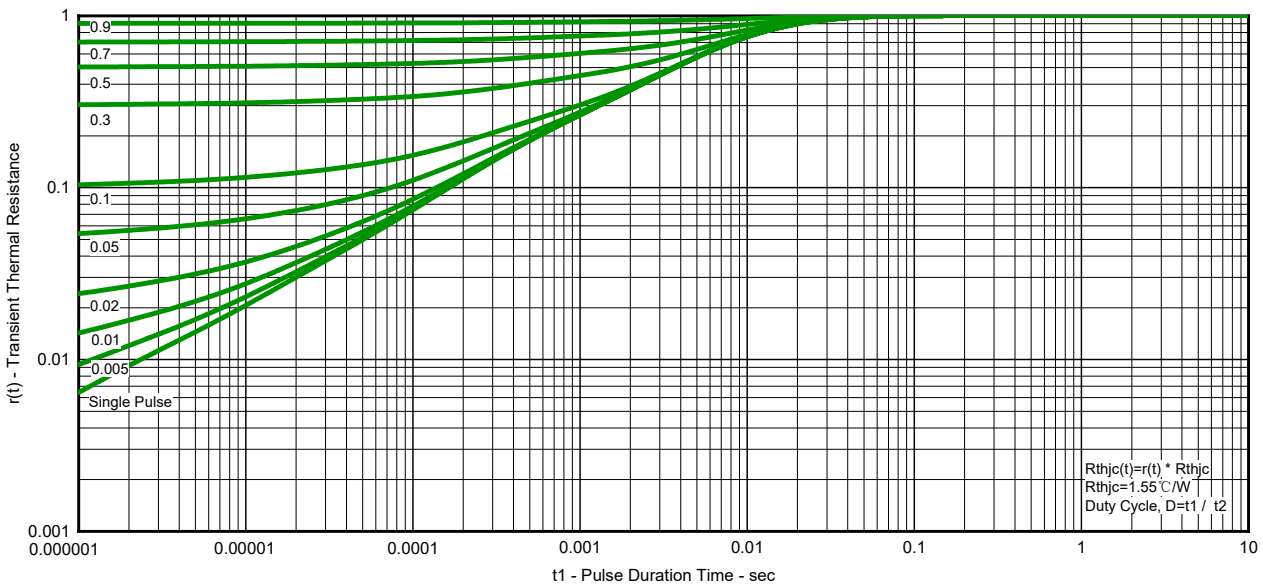
**Fig.7 Gate Charge Characteristics**



**Fig.8 Typical Junction Capacitance**

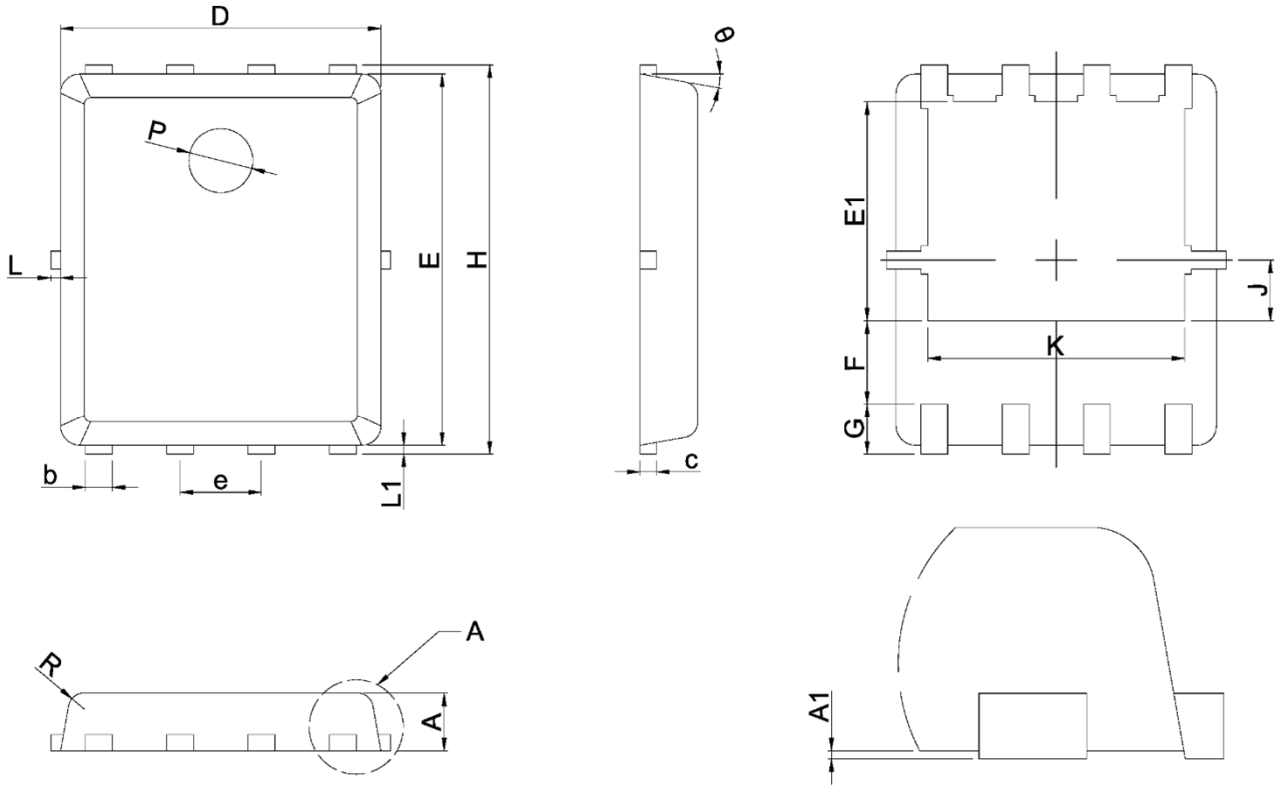


**Fig.9 Safe Operation Area**



**Fig.10 Transient Thermal Resistance**

Product Dimension (PDFN5060-8L)



DETAIL "A"

Dim	Millimeters		Inches	
	Min	Max	Min	Max
A	0.80	1.00	0.031	0.039
A1	0.00	0.05	0.000	0.002
b	0.35	0.49	0.014	0.019
c	0.254 Ref.		0.010 Ref.	
D	4.90	5.10	0.193	0.201
E	5.70	5.90	0.224	0.232
E1	3.35	3.65	0.132	0.144
e	1.27 BSC.		0.050 BSC.	
F	1.40 Ref.		0.055 Ref.	
G	0.60 Ref.		0.024 Ref.	
H	5.95	6.20	0.234	0.244
J	0.95 BSC.		0.037 BSC.	
K	4.00 Ref.		0.157 Ref.	
L	-	0.15	-	0.006
L1	0.10	0.18	0.004	0.007
P	1.00 Ref.		0.039 Ref.	
R	0.25 Ref.		0.010 Ref.	
$\theta$	6°	14°	6°	14°

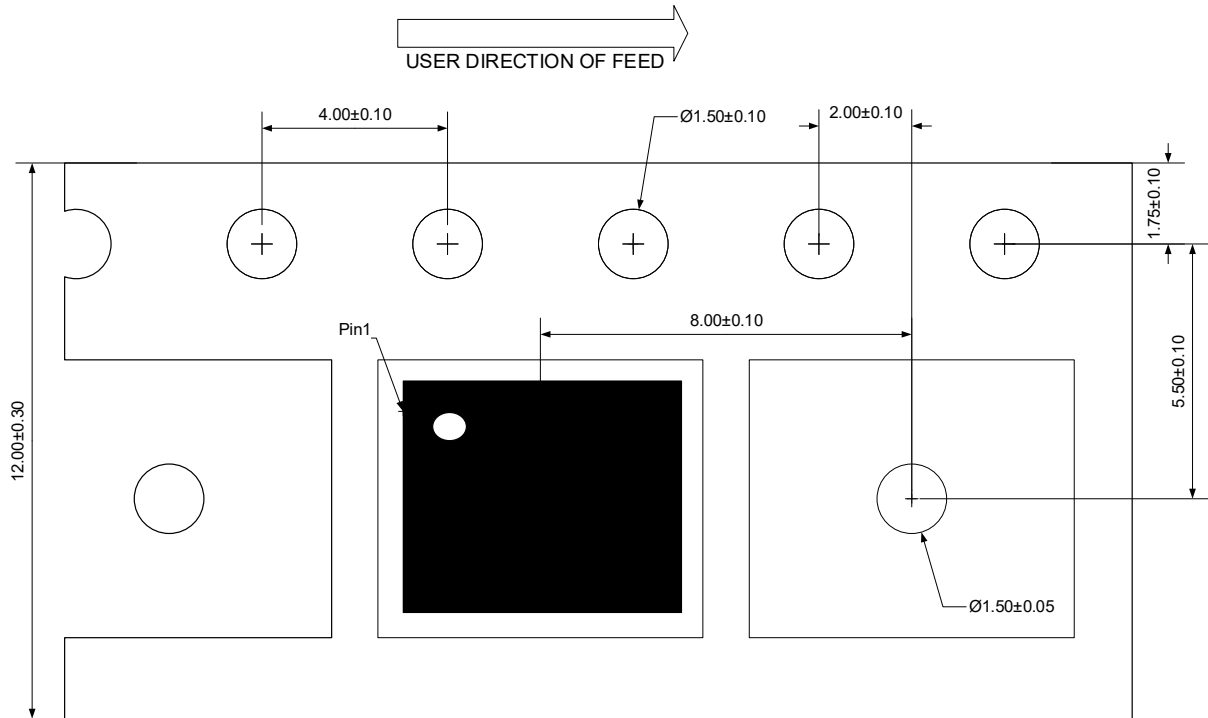
# N-Channel MOSFET

# PSM8N10R12D

## Ordering Information


Device	Package	Reel	Shipping
PSM8N10R12D	PDFN5060-8L	13"	5000 / Tape & Reel

## Load With Information



Unit:mm


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